

# Critical layer thickness determination for GaN thin films grown on sapphire substrate via hollow-cathode plasma-assisted atomic layer deposition

Mustafa Alevli, Nese Gungor, and Necmi Biyikli

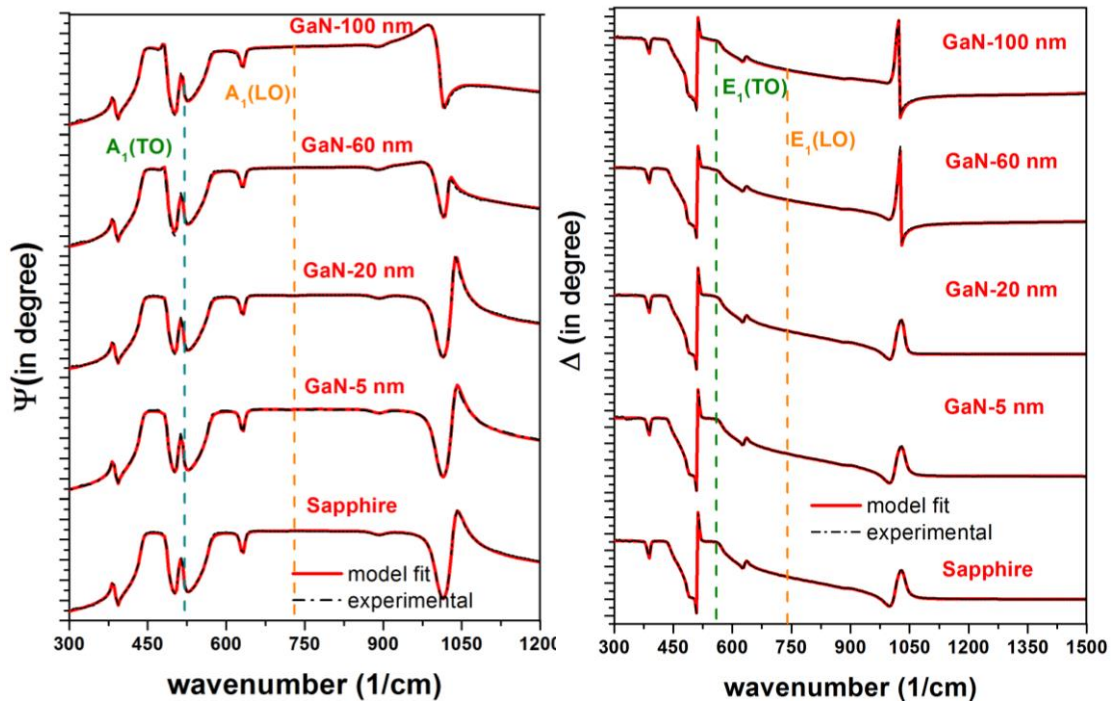


Figure 1. Model of psi and delta versus wavenumber for PEALD GaN films grown on sapphire

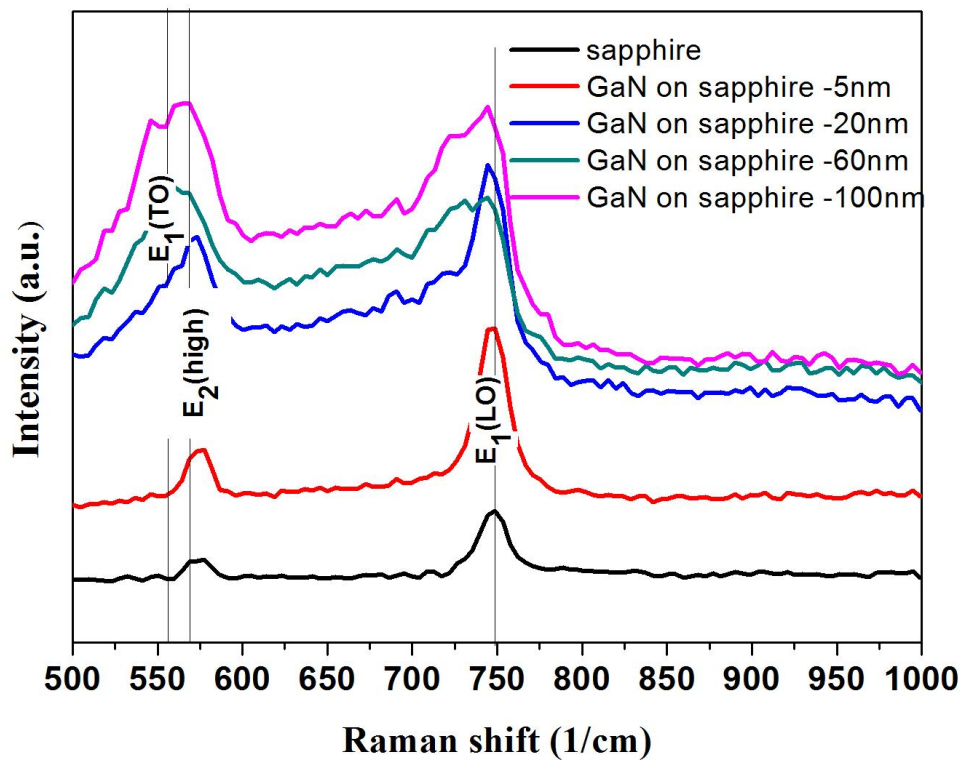


Figure 2. Raman spectra with 633 nm excitation for various GaN film thicknesses.